

# MA724

## Silicon epitaxial planer type

For super high-speed switching circuit  
For small current rectification

### ■ Features

- Two elements are incorporated in MA721 (of a type in the same direction)
- $I_{F(AV)} = 200\text{mA}$  rectification possible
- Superior in reliability

### ■ Absolute Maximum Ratings (Ta= 25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	30	V
Repetitive peak reverse voltage	$V_{RRM}$	30	V
Peak forward current	Single	300	mA
	Double	225*1	
Average forward current	Single	200	mA
	Double	150*1	
Non-repetitive peak forward surge current	Single	1	A
	Double	0.75*1	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	- 55 to + 150	°C

\*1 Use value per chip

\*2 50Hz sine wave, one-cycle wave, high value (non-repetitive)

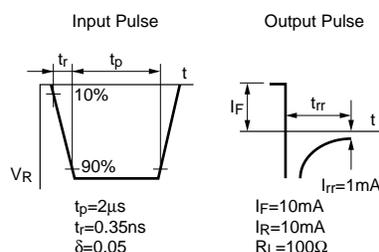
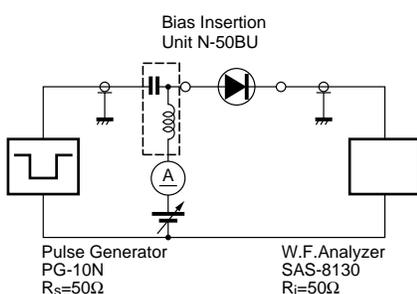
### ■ Electrical Characteristics (Ta= 25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	$I_R$	$V_R = 30\text{V}$			50	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 200\text{mA}$			0.55	V
Terminal capacitance	$C_t$	$V_R = 0\text{V}, f = 1\text{MHz}$		30		pF
Reverse recovery time	$t_{rr}^*$	$I_F = I_R = 100\text{mA}$ $I_{rr} = 10\text{mA}, R_L = 100\Omega$		3.0		ns

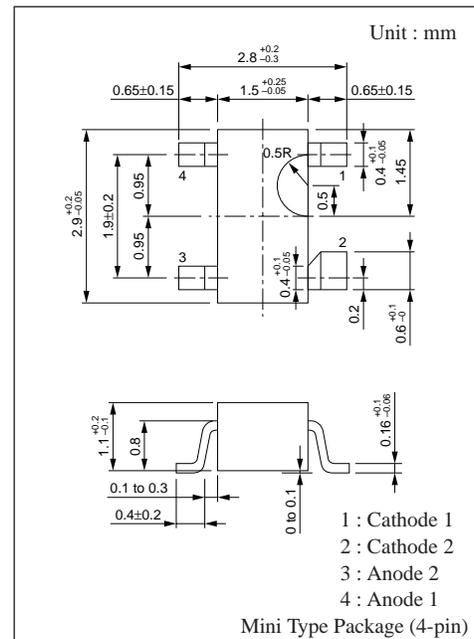
Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Rated input/output frequency : 1000MHz

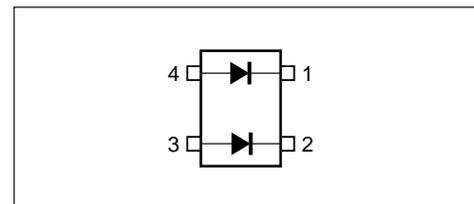
3. \*  $t_{rr}$  measuring circuit



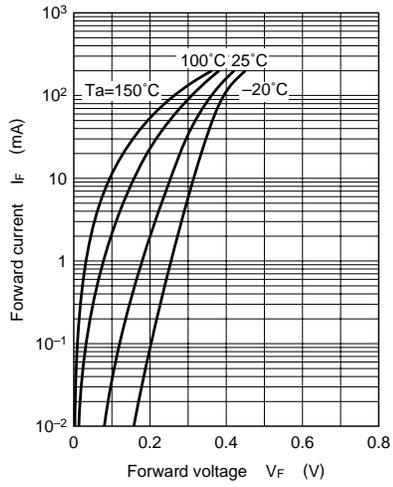
### ■ Marking



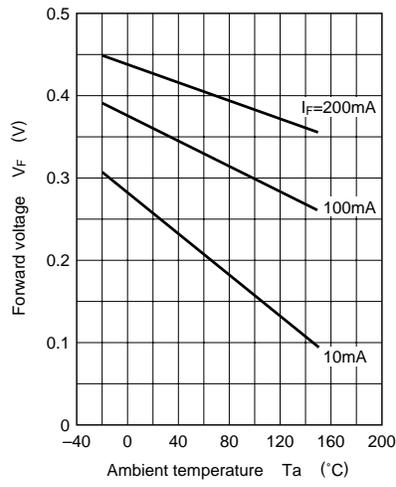
### ■ Internal Connection



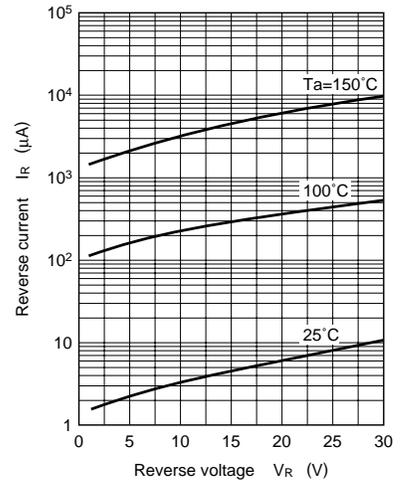
$I_F - V_F$



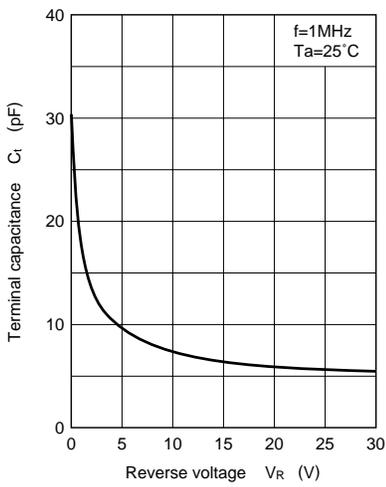
$V_F - T_a$



$I_R - V_R$



$C_t - V_R$



$I_R - T_a$

